US00D949808S

(12) **United States Design Patent**
Maeda

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(45) **Date of Patent: ** Apr. 26, 2022**

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(54) **SEMICONDUCTOR DEVICE**

(71) Applicant: **Sansha Electric Manufacturing Co., Ltd.**, Osaka (JP)

(72) Inventor: **Kotaro Maeda**, Osaka (JP)

(73) Assignee: **SANSHA ELECTRIC MANUFACTURING CO., LTD.**, Osaka (JP)

(**) Term: **15 Years**

(21) Appl. No.: **29/760,010**

(22) Filed: **Nov. 27, 2020**

(51) **LOC (13) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/123, 133, 146, 147, 158, 182, 184, D13/199
CPC H01L 28/06; H01L 28/07; H01L 28/08; H01L 25/07; H01L 25/16; H01L 25/18; H01L 23/00; H01L 23/31; H05K 1/18; H05K 7/00; H05K 7/20; H02M 7/00
See application file for complete search history.

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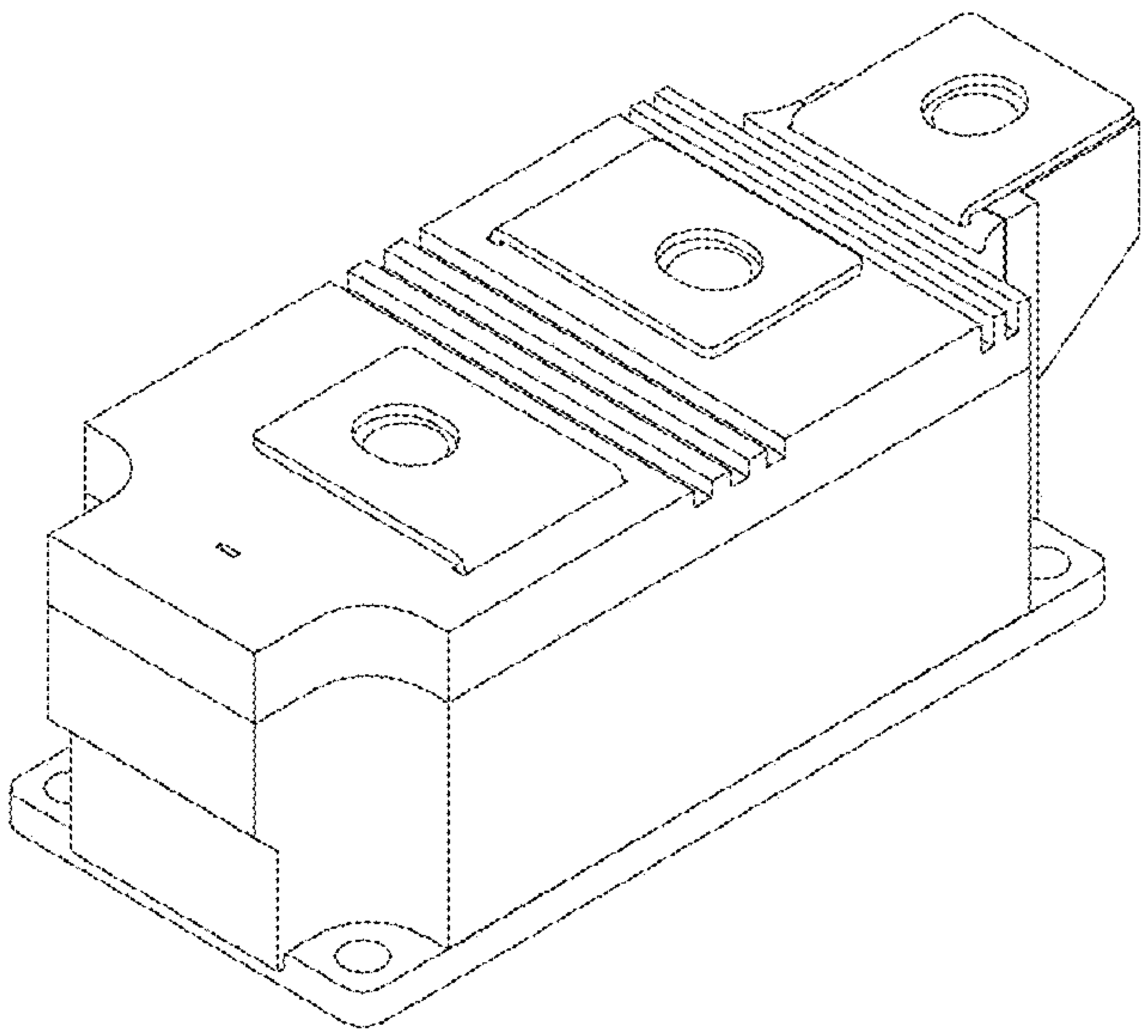
(57) **CLAIM**

The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. **1** is a front view of the semiconductor device, showing my new design;
FIG. **2** is a rear view thereof;
FIG. **3** is a right-side view thereof;
FIG. **4** is a left-side view thereof;
FIG. **5** is a top view thereof;
FIG. **6** is a bottom view thereof;
FIG. **7** is a front top right side perspective view thereof;
FIG. **8** is a rear bottom left side perspective view thereof;
FIG. **9** is a front top left side perspective view thereof; and,
FIG. **10** is a rear bottom right side perspective view thereof.
The broken lines in the drawings illustrate portions of the semiconductor device that form no part of the claimed design.

1 Claim, 10 Drawing Sheets



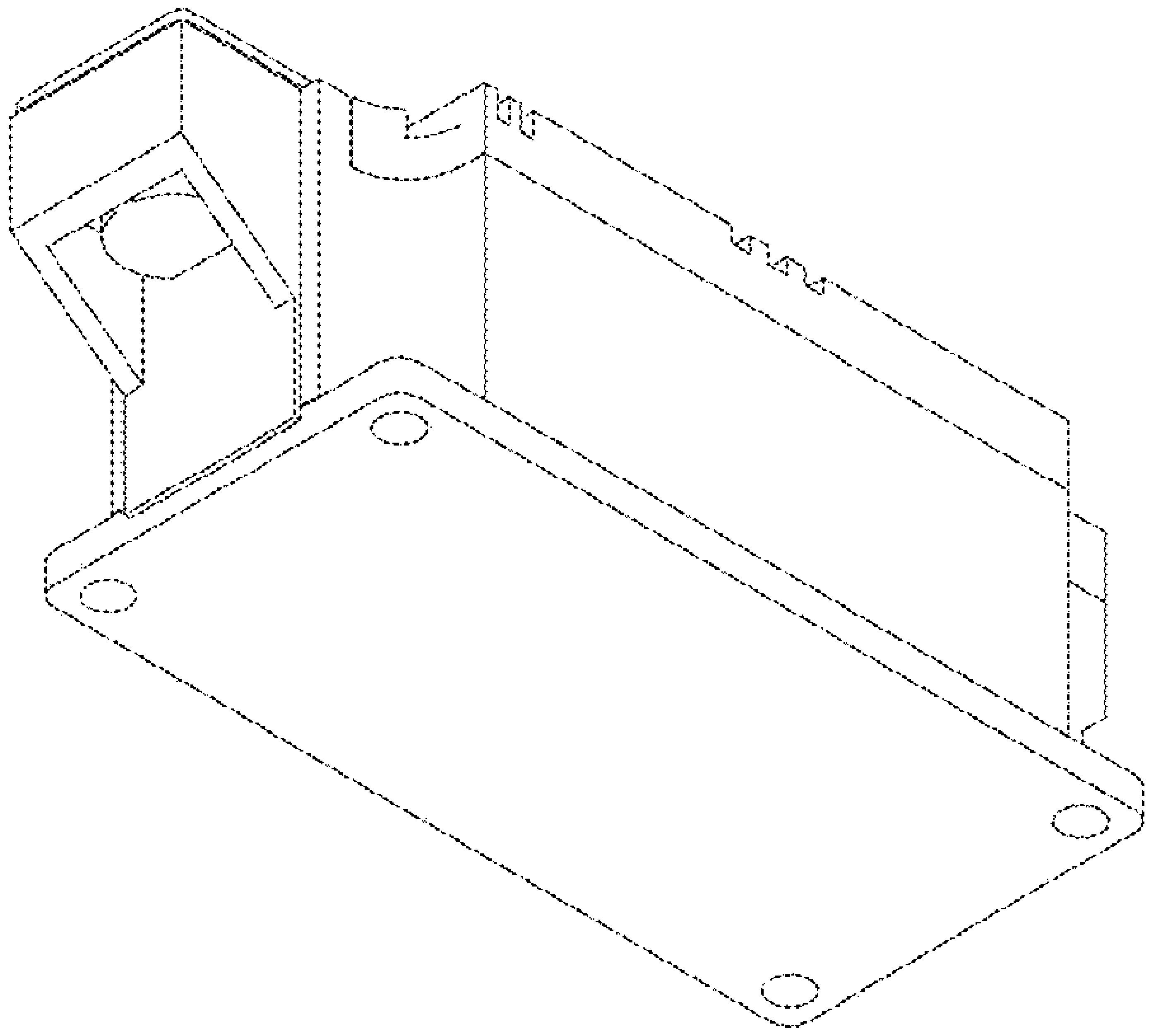


FIG. 1

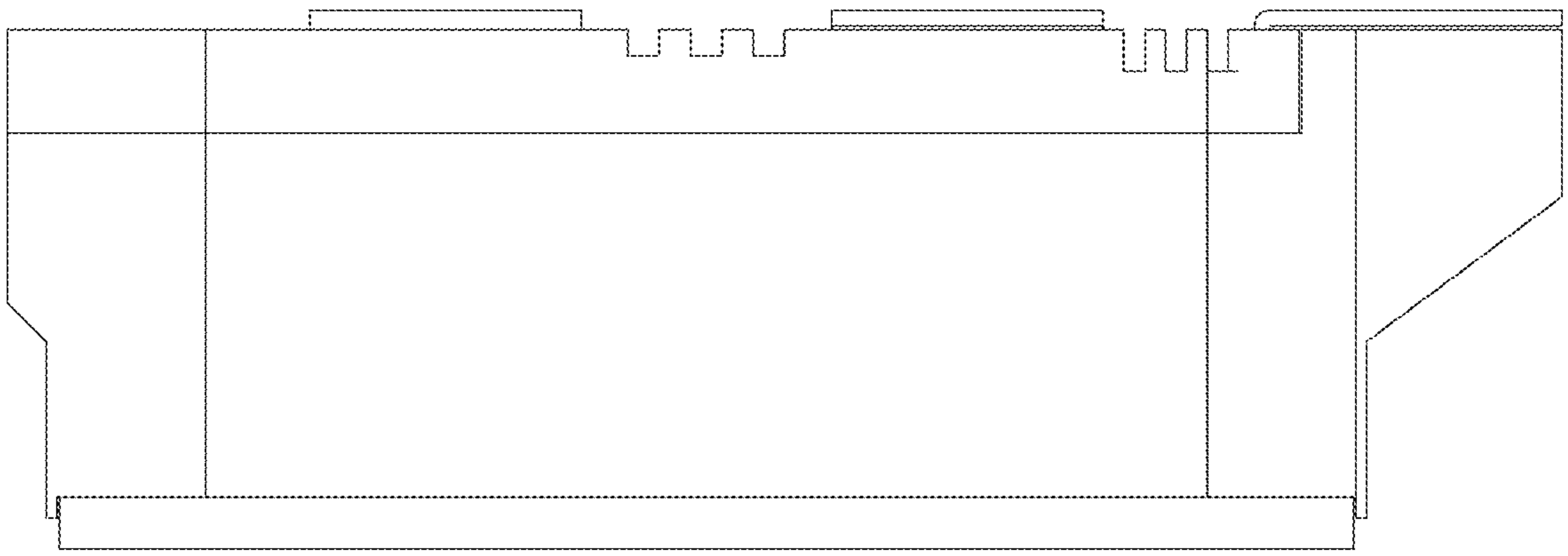


FIG. 2

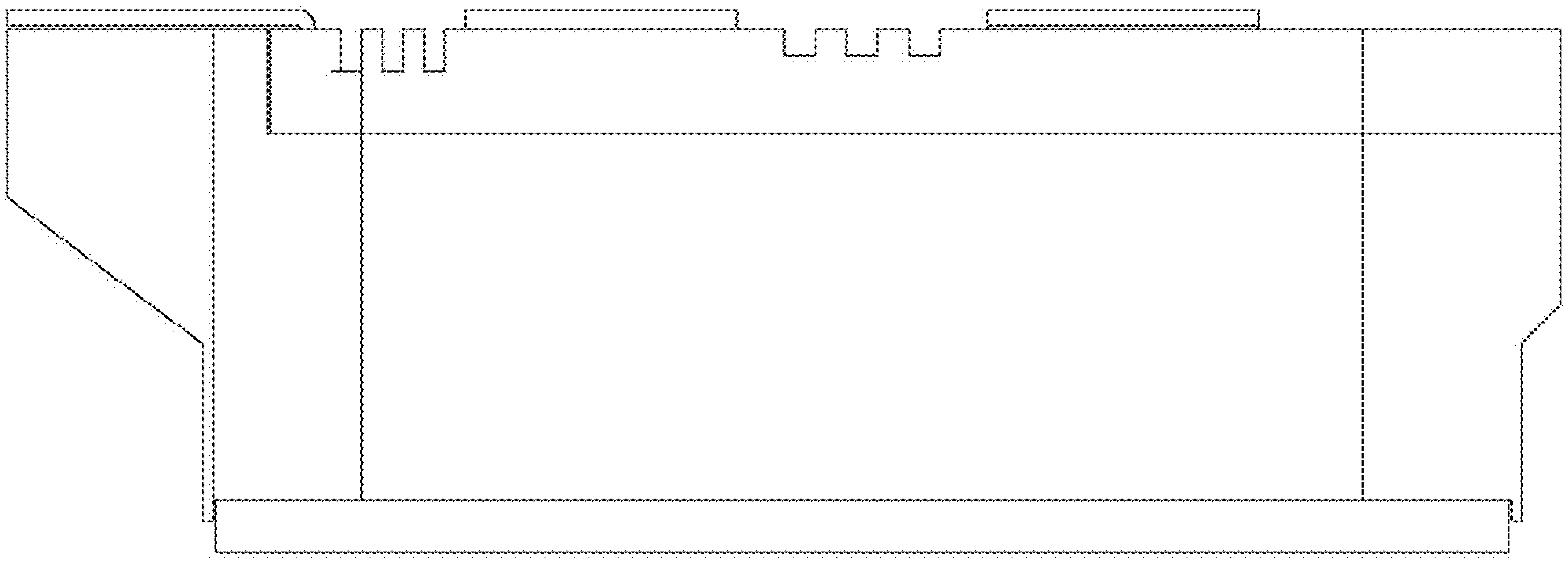


FIG. 3

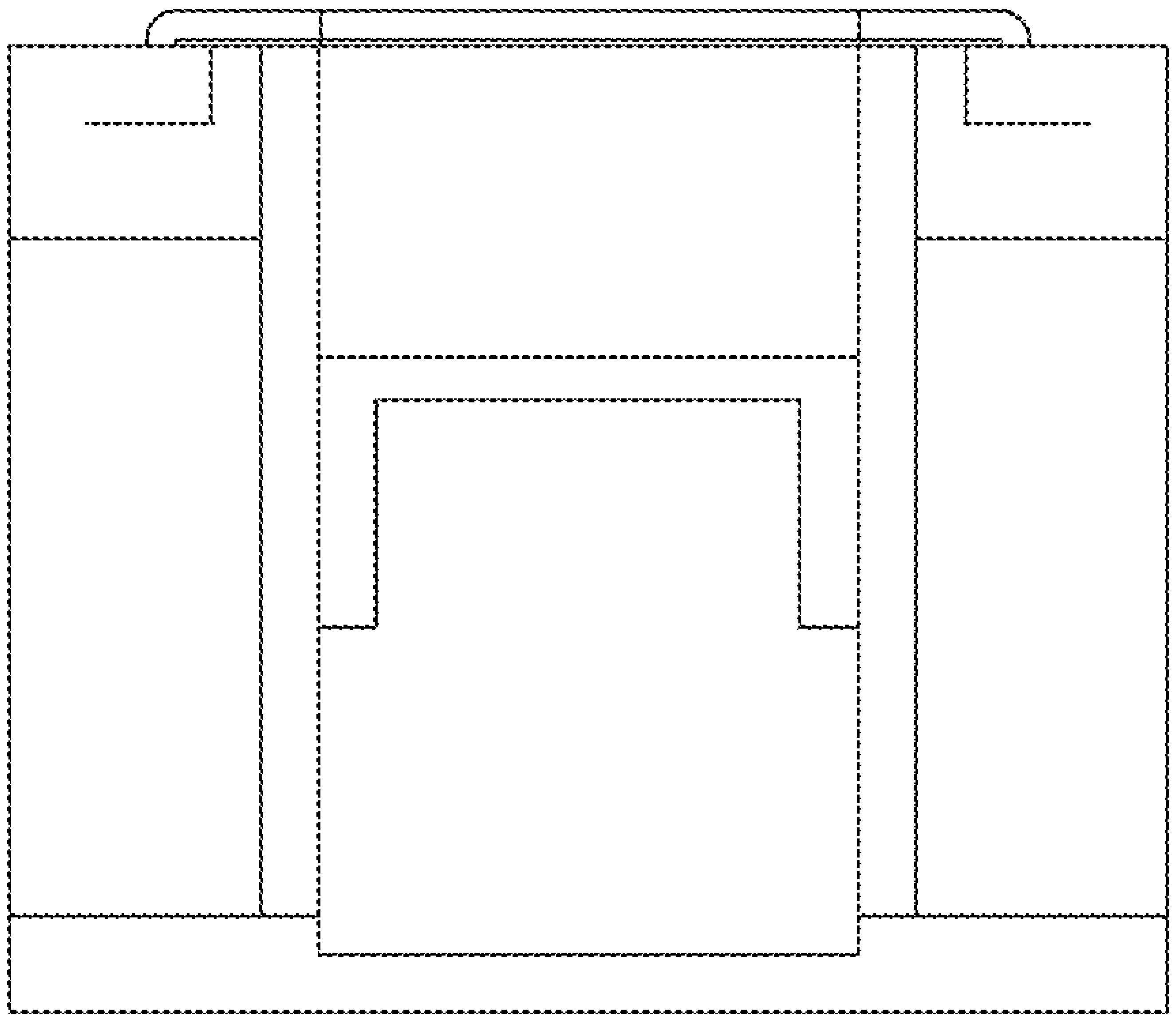


FIG. 4

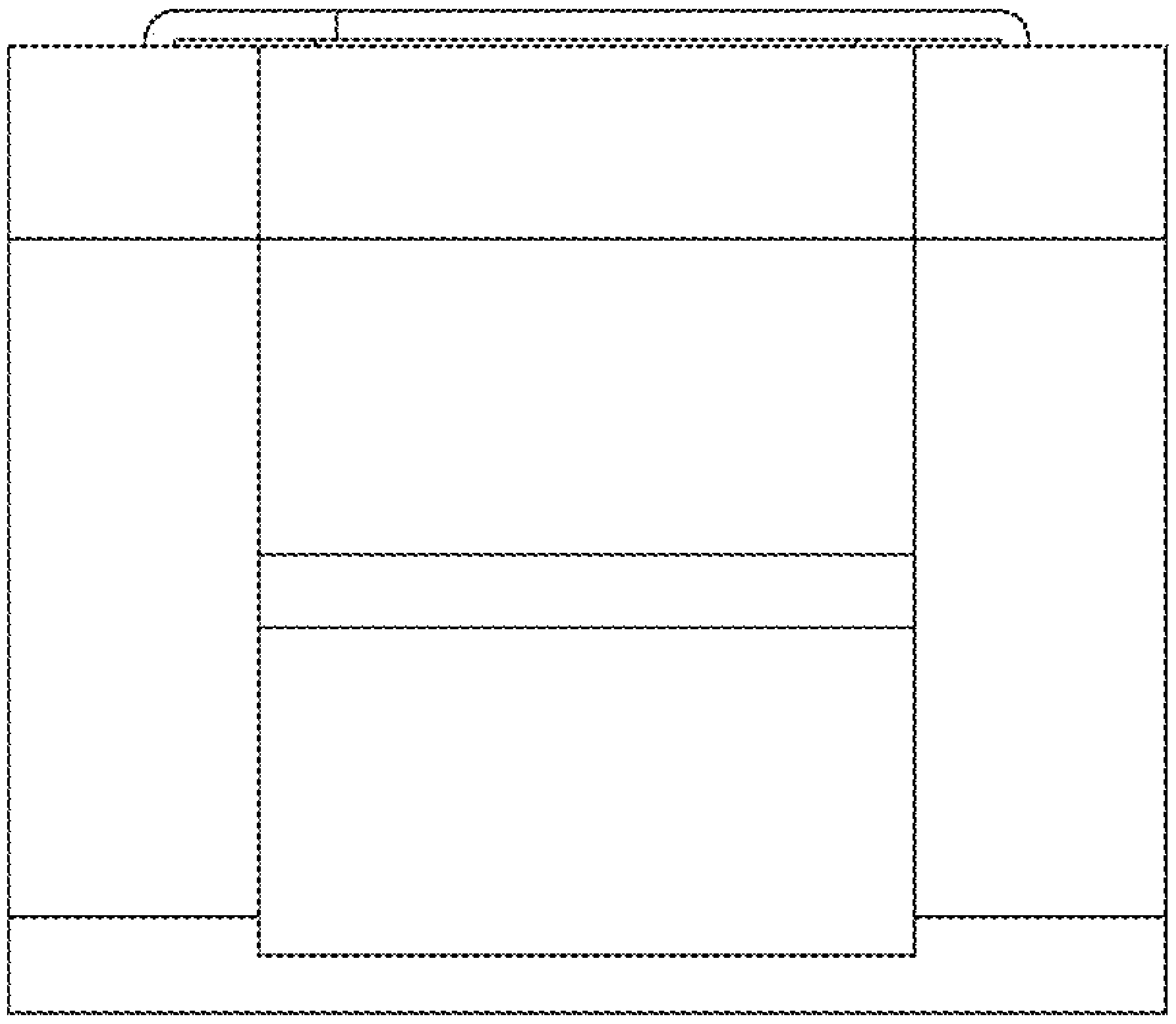


FIG. 5

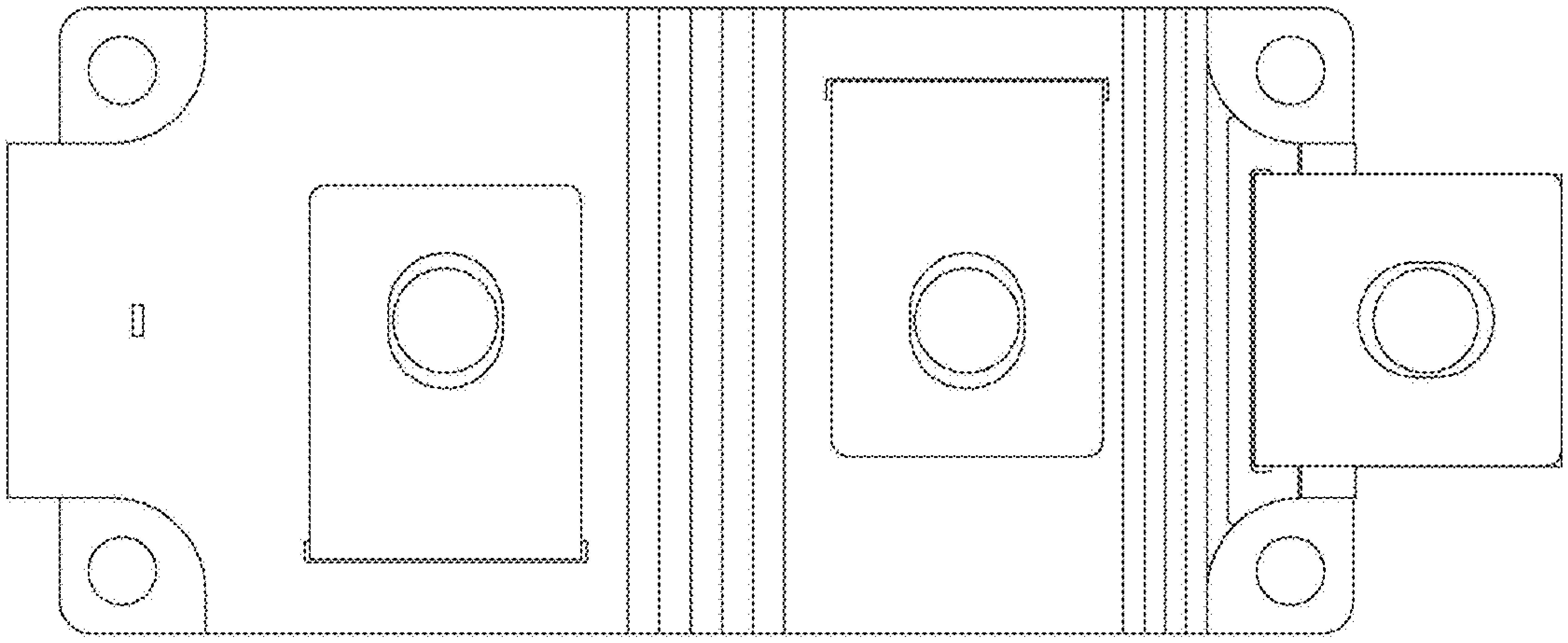


FIG. 6

FIG. 7

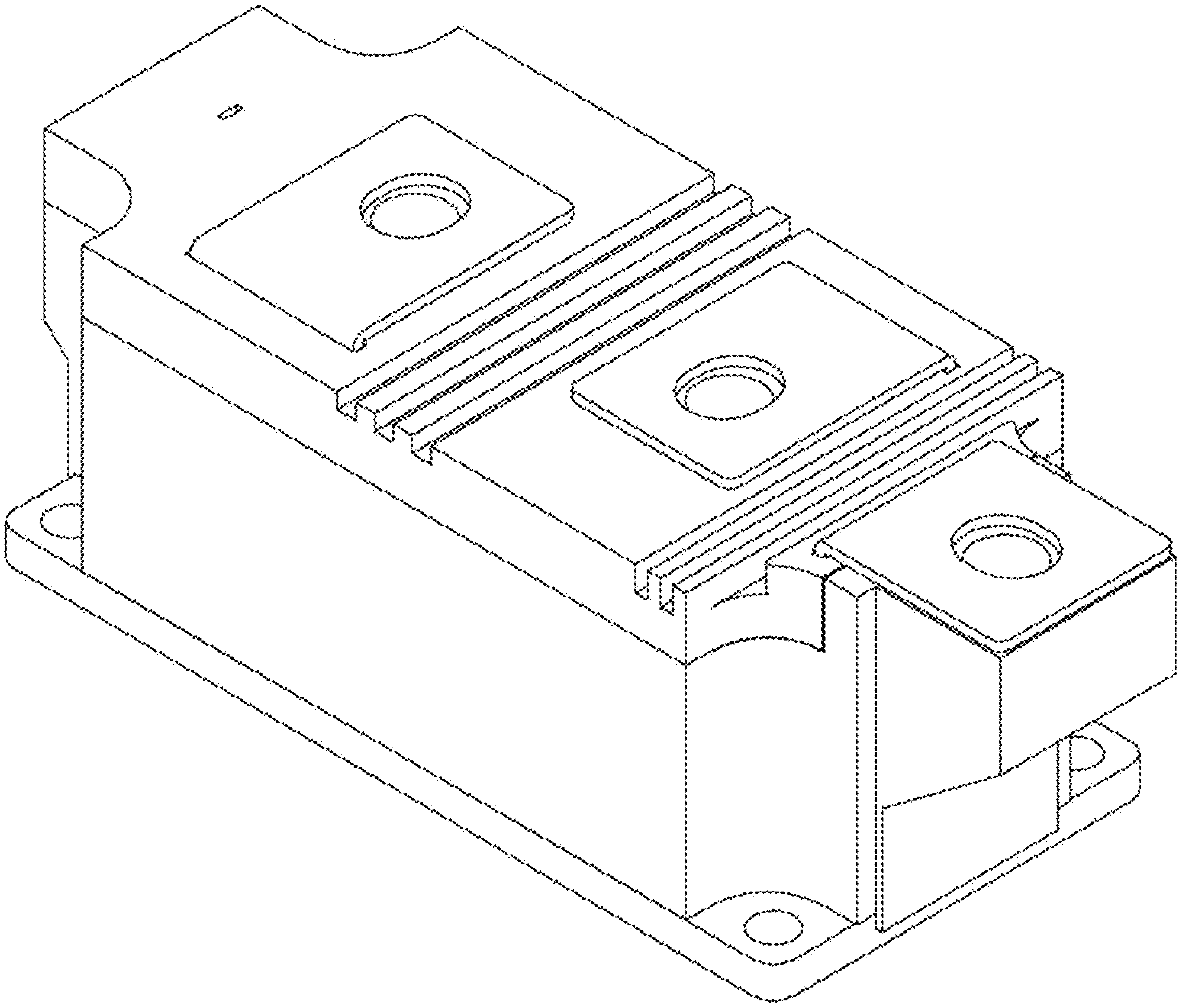


FIG. 8

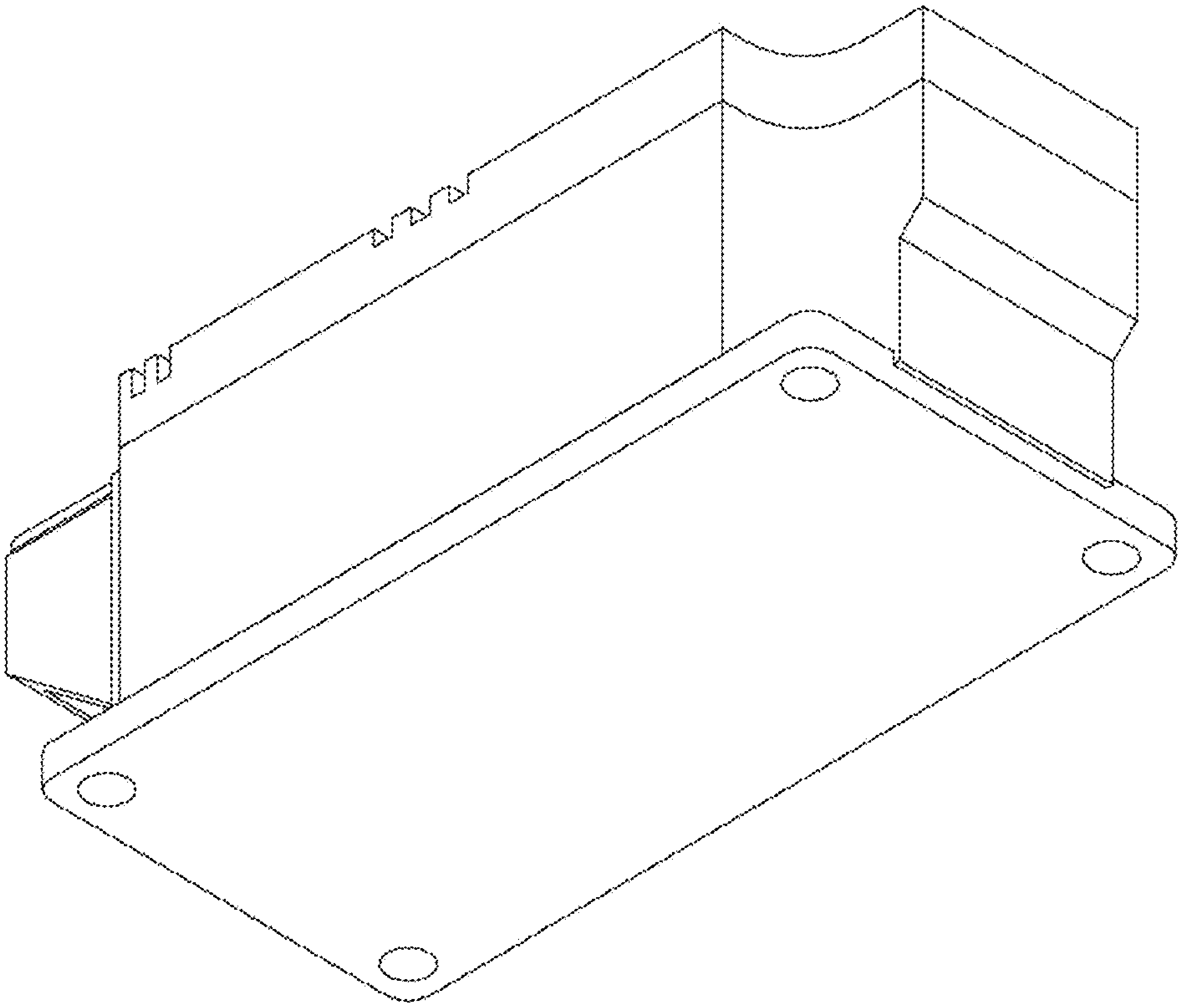


FIG. 9

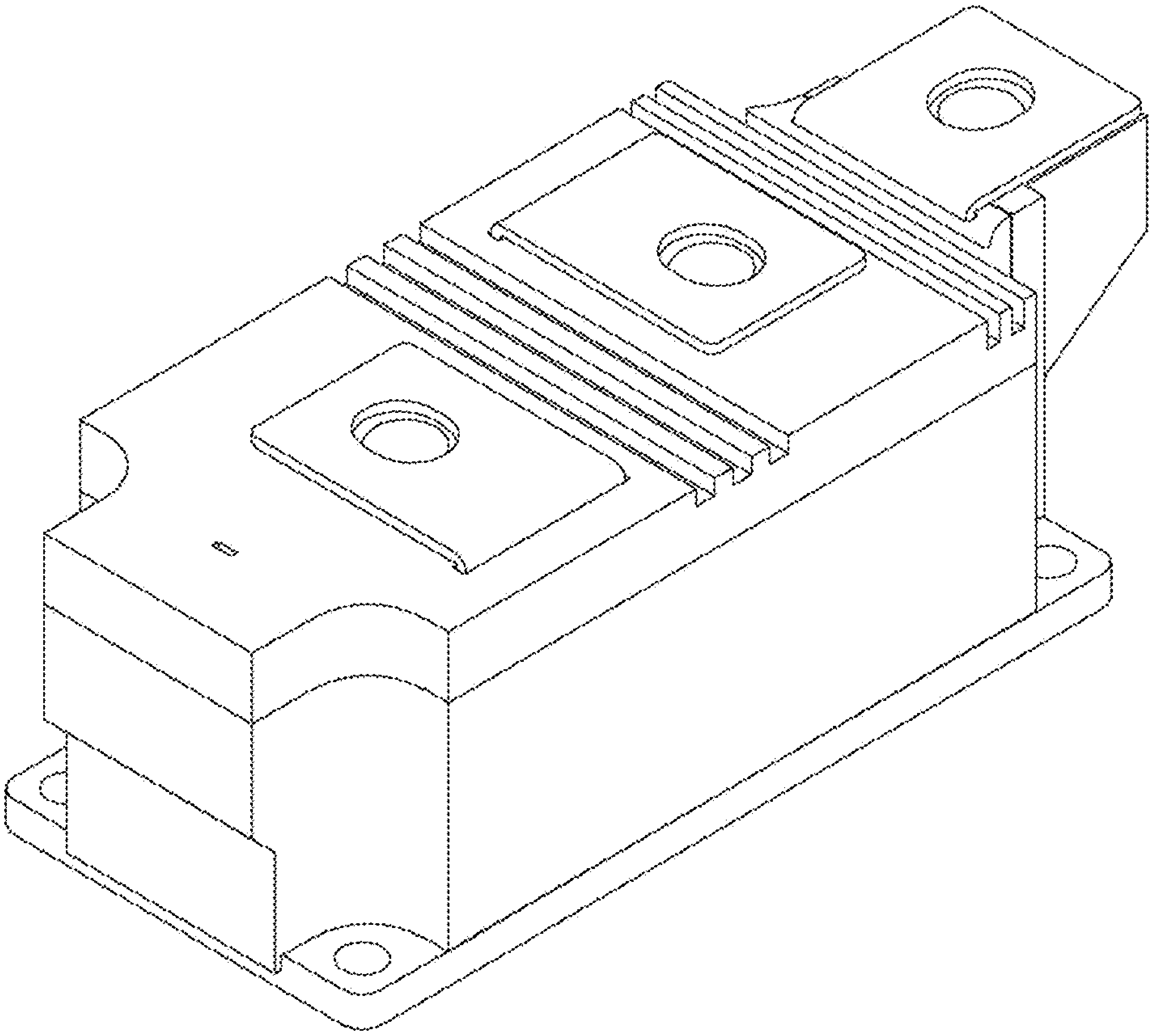


FIG. 10